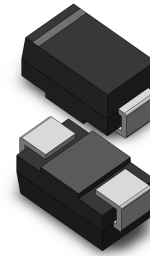


VOLTAGE RANGE: 150 - 200V
CURRENT: 1.0 A

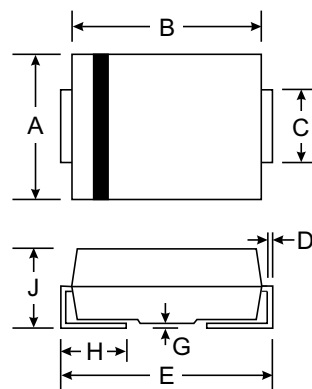


Features

- Schottky Barrier Chip
- Ideally Suited for Automatic Assembly
- Low Power Loss, High Efficiency
- For Use in Low Voltage Application
- Guard Ring Die Construction
- Plastic Case Material has UL Flammability Classification Rating 94V-O

Mechanical Data

- Case: SMA/DO-214AC, Molded Plastic
- Terminals: Solder Plated, Solderable per MIL-STD-750, Method 2026
- Polarity: Cathode Band or Cathode Notch
- Marking: Type Number
- Weight: 0.064 grams (approx.)



SMA(DO-214AC)		
Dim	Min	Max
A	2.29	2.92
B	4.00	4.60
C	1.27	1.63
D	0.15	0.31
E	4.80	5.59
G	0.10	0.20
H	0.76	1.52
J	2.01	2.62
All Dimensions in mm		

Maximum Ratings and Electrical Characteristics T_A = 25°C unless otherwise specified

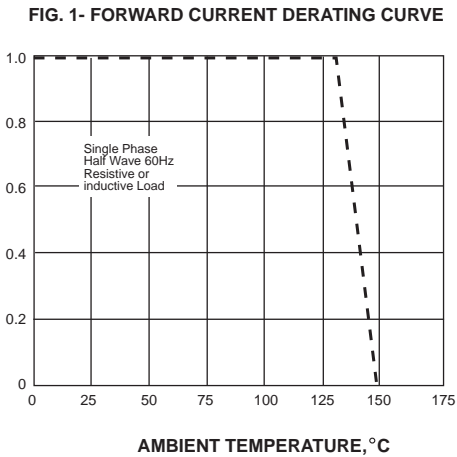
Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	B1150A	B1200A	Unit
Maximum repetitive peak reverse voltage	V _{RRM}	150	200	V
Maximum RMS voltage	V _{RMS}	105	140	V
Maximum DC blocking voltage	V _{DC}	150	200	V
Maximum average forward rectified current at T _L (see fig.1)	I _(AV)	1.0		A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	30.0		A
Maximum instantaneous forward voltage at 1.0A	V _F	0.85	0.95	V
Maximum DC reverse current T _A =25°C at rated DC blocking voltage T _A =100°C	I _R	0.2 2.0		mA
Typical junction capacitance (NOTE 1)	C _J	90		pF
Typical thermal resistance (NOTE 2)	R _{θJA}	88.0		°C/W
Operating junction temperature range	T _J	-50 to +150		°C
Storage temperature range	T _{STG}	-50 to +150		°C

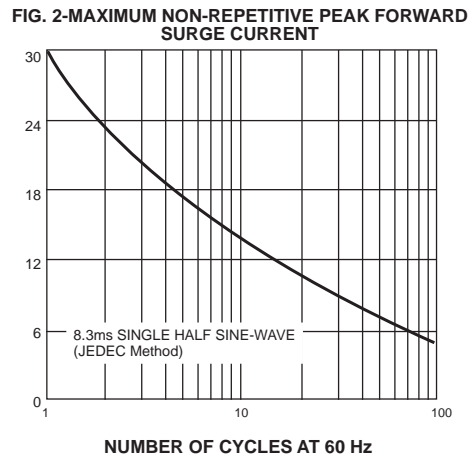
Note: 1. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
 2. P.C.B. mounted with 0.2x0.2" (5.0x5.0mm) copper pad areas

RATINGS AND CHARACTERISTIC CURVES B1150A THRU B1200A

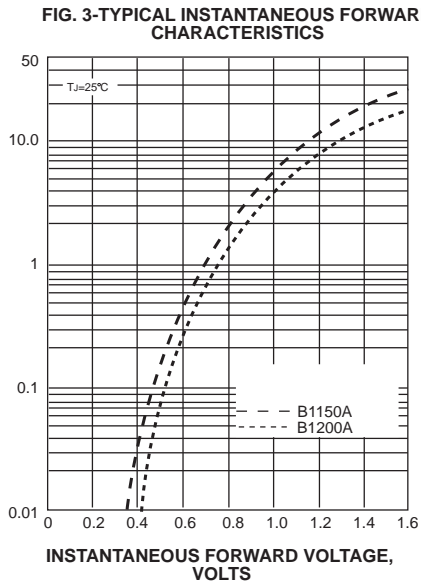
AVERAGE FORWARD RECTIFIED CURRENT, AMPERES



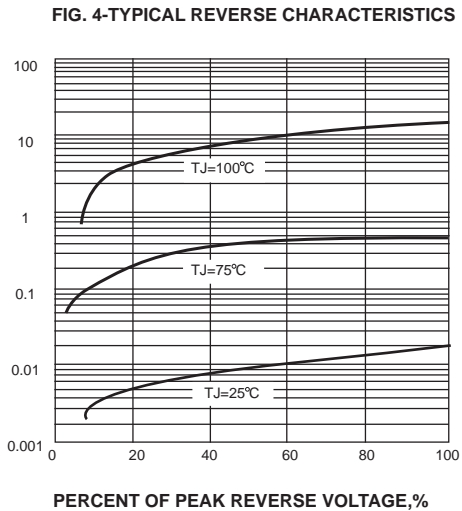
PEAK FORWARD SURGE CURRENT, AMPERES



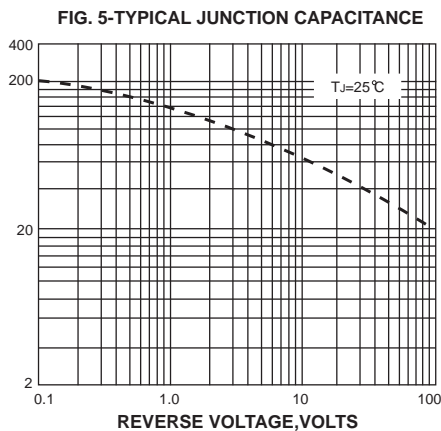
INSTANTANEOUS FORWARD CURRENT, AMPERES



INSTANTANEOUS REVERSE CURRENT, MILLIAMPERES



JUNCTION CAPACITANCE, pF



TRANSIENT THERMAL IMPEDANCE, °C/W

